

## **Diode Chip**

# **DTHP 19-065**

## tentative

### **Circuit Diagram**



#### Applications

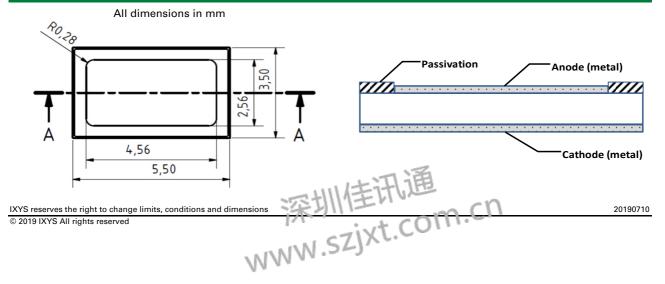
- antiparallel diode for high frequency switching
- antisaturation diode
- snubber diode
- freewheeling diode in converters & motor control
- · rectifiers in switch mode power supplies (SMPS) • inductive heating & melting
- uninterruptible power supplies (UPS)
- ultrasonic cleaners & welders

### Mechanical Characteristic

Characteristic Conditions Value Unit Area active 13,82 mm<sup>2</sup> Area total 19,25 mm<sup>2</sup> Thickness 70 μm Wafer size Ø 150 mm Die Per Wafer 698 Material Si Passivation front side SiN Metalisation front side bondable: AI Al/Ti/NiV/Ag Metalisation back side solderable (only): Recom. wire bonds (AI) Anode Number 5 \*= stitch bonds Ø 380 μm Reject ink dot size Ø 0.4 - 1.0 mm °C Recom. solder temp. <300 Recom. Storage environment sawn on foil in org. container, in dry nitrogen <6 month unsawn wafer in org. container, in dry nitrogen <2 year in waffle pack in org. container, in dry nitrogen <2 year -40...40 °C

Storage temp.

#### **Dimensions**



#### **Product Summary**

Characteristics	Value	Unit		
V <sub>RRM</sub>	650	V		
I F <sub>(AV)</sub>	54	Α		
Chip Dimensions	5,5x3,5	mm		
unsawn wafer	Contact Bare	Contact Bare Die Sales		
sawn on foil	Yes			
in waffle pack	Yes			

#### **Features**

- fast, soft SONIC diode
- high ruggedness
- low forward voltage drop • small temp. Coefficient
- · low switching losses
- anode top
- Tvjm = 175°C



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### **Electrical Parameters**

Symbol	Conditions		Value					
		Min	Тур	Max	Unit			
Static Characteristics								
I <sub>R</sub>	$V = V_{RRM}$	Tvj = 25°C			50	μA		
		Tvj = 150°C		0,5		mA		
V <sub>F</sub>	lf = 60A	Tvj = 25°C		1,40	1,60	V		
		Tvj = 150°C		1,35		V		
V <sub>F0</sub>	For power loss calculations only				1	V		
r <sub>F</sub>		Tvj = 175°C			8,3	mΩ		
T <sub>VJ</sub>			-55		175	°C		
I <sub>F(AV)</sub> *	DC	$Tc = 80^{\circ}C$		54		А		
I <sub>FSM</sub> *	V = 0V	Tvj = 45°C			250	А		
R <sub>thJC</sub> *	DC current				1,2	K/W		

#### **Dynamic Characteristics**

<i>Q</i> <sub><i>rr</i></sub>			-	μC
I <sub>RM</sub>	V = 300V	Tvj = 25°C	-	A
t <sub>rr</sub>	lf = 50A	dlf/dt = 1200A/µs	-	ns
E rec			-	mJ
Q <sub>rr</sub>			4	μC
I <sub>RM</sub>	V = 300V	Tvj = 150°C	50	A
t <sub>rr</sub>	lf = 50A	dlf/dt = 1200A/µs	150	ns
E <sub>rec</sub>			0,7	mJ
* D		Dut		

\* Data according to assembled 380µm DCB

Data according to IEC 60747

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